



BD644/646/648/650/652

SILICON DARLINGTON POWER TRANSISTORS

PNP epitaxial-base transistors in a monolithic Darlington circuit and housed in a TO-220 enveloppe. They are intended for output stages in audio equipment, general amplifiers, and analogue switching application.

NPN complements are BD643, BD645, BD647, BD649 and BD651

ABSOLUTE MAXIMUM RATINGS

Symbol	Ratings	Value	Unit
$-V_{CBO}$	Collector-Base Voltage	BD644	45
		BD646	60
		BD648	80
		BD650	100
		BD652	120
$-V_{CEO}$	Collector-Emitter Voltage	BD644	45
		BD646	60
		BD648	80
		BD650	100
		BD652	120
$-V_{EBO}$	Emitter-Base Voltage	BD644	5
		BD646	
		BD648	
		BD650	
		BD652	
I_C	Collector Current	BD644	8
		BD646	
		BD648	
		BD650	
		BD652	
I_{CM}	Collector Peak Current	BD644	12
		BD646	
		BD648	
		BD650	
		BD652	



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Symbol	Ratings		Value	Unit
-I _B	Base Current	BD644 BD646 BD648 BD650 BD652	150	mA
P _T	Power Dissipation	@ T _{mb} < 25° BD644 BD646 BD648 BD650 BD652	62.5	Watts
T _J	Junction Temperature	BD644 BD646 BD648 BD650 BD652	150	°C
T _s	Storage Temperature range	BD644 BD646 BD648 BD650 BD652	-65 to +150	

Limiting values in accordance with the Absolute Maximum System (IEC 134)

THERMAL CHARACTERISTICS

Symbol	Ratings	Value	Unit
R _{thJ-MB}	From junction to mounting base BD644 BD646 BD648 BD650 BD652	2	K/W
R _{thJ-A}	From junction to ambient in free air BD644 BD646 BD648 BD650 BD652	70	K/W



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ELECTRICAL CHARACTERISTICS

TC=25°C unless otherwise noted

Symbol	Ratings	Test Condition(s)	Min	Typ	Mx	Unit
$-I_{CBO}$	Collector Cutoff Current	$-I_E=0, -V_{CB} = -V_{CEO}MAX$	BD644	-	0.1	mA
			BD646			
			BD648			
			BD650			
			BD652			
		$-I_E=0, -V_{CB} = 1/2 -V_{CBO}MAX, T_J=150^\circ C$	BD644	-	1	mA
			BD646			
			BD648			
			BD650			
			BD652			
$-I_{CEO}$	Collector Cutoff Current	$-I_E=0, -V_{CE} = 1/2 -V_{CEO}MAX$	BD644	-	0.2	mA
			BD646			
			BD648			
			BD650			
			BD652			
$-I_{EBO}$	Emitter Cutoff Current	$-V_{EB}=5 V, -I_C=0$	BD644	-	5.0	mA
			BD646			
			BD648			
			BD650			
			BD652			
	Collector-Emitter saturation Voltage (*)	$-I_C=4 A, -I_B=16 mA$	BD644	-	-	2
			BD646	-	-	-
			BD648	-	-	-
			BD650	-	-	-
			BD652	-	-	-
$-V_{CE(SAT)}$	Collector-Emitter saturation Voltage (*)	$-I_C=3 A, -I_B=12 mA$	BD644	-	-	-
			BD646	-	-	2
			BD648	-	-	2
			BD650	-	-	2
			BD652	-	-	2
	Collector-Emitter saturation Voltage (*)	$-I_C=5 A, -I_B=50 mA$	BD644	-	-	2.5
			BD646	-	-	2.5
			BD648	-	-	2.5
			BD650	-	-	2.5
			BD652	-	-	2.5
$-V_{BE(SAT)}$	Base-Emitter Saturation Voltage (*)	$-I_C=12 A, -I_B=50 mA$	BD644	-	3	V
			BD646			
			BD648			
			BD650			
			BD652			



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Symbol	Ratings	Value			Unit
$-V_{BE}$	$-I_C=4\text{ A}, -V_{CE}=3\text{ V}$ Base-Emitter Voltage (*)	BD644	-	-	2.5
		BD646	-	-	-
		BD648	-	-	-
		BD650	-	-	-
		BD652	-	-	-
	$-I_C=3\text{ A}, -V_{CE}=3\text{ V}$	BD644	-	-	-
		BD646	-	-	2.5
		BD648	-	-	2.5
		BD650	-	-	2.5
		BD652	-	-	2.5
h_{FE}	$-V_{CE}=3.0\text{ V}, -I_C=0.5\text{ A}$ DC Current Gain (*)	BD644	-	2700	-
		BD646	-		-
		BD648	-		-
		BD650	-		-
		BD652	-		-
	$-V_{CE}=3.0\text{ V}, -I_C=4\text{ A}$	BD644	750	-	-
		BD646	-	-	-
		BD648	-	-	-
		BD650	-	-	-
		BD652	-	-	-
	$-V_{CE}=3.0\text{ V}, -I_C=3\text{ A}$	BD644	-	750	-
		BD646	-		-
		BD648	-		-
		BD650	-		-
		BD652	-		-
	$-V_{CE}=3.0\text{ V}, -I_C=8\text{ A}$	BD644	-	200	-
		BD646	-		-
		BD648	-		-
		BD650	-		-
		BD652	-		-
h_{fe}	$-V_{CE}=3.0\text{ V}, -I_C=4\text{ A}, f=1\text{MHz}$ Small Signal Current Gain	BD644	10	-	-
		BD646	-	-	-
		BD648	-	-	-
		BD650	-	-	-
		BD652	-	-	-
	$-V_{CE}=3.0\text{ V}, -I_C=3\text{ A}, f=1\text{MHz}$	BD644	-	-	-
		BD646	10	-	-
		BD648	10	-	-
		BD650	10	-	-
		BD652	10	-	-
t_{on}	turn-on time	$-I_C=3\text{ A}, -I_{Bon}=I_{Boff}=12\text{ mA}$	All types	1	μs
t_{off}	turn-off time		All types	5	μs

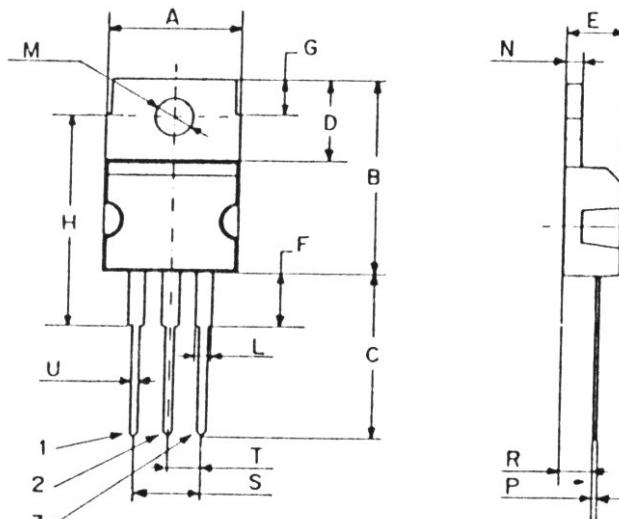
(*) Pulse Width $\approx 300\text{ }\mu\text{s}$, Duty Cycle $\angle 2.0\%$



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MECHANICAL DATA CASE TO-220

DIMENSIONS		
	mm	inches
A	9,86	0,39
B	15,73	0,62
C	13,37	0,52
D	6,67	0,26
E	4,44	0,17
F	4,21	0,16
G	2,99	0,11
H	17,21	0,68
L	1,29	0,05
M	3,6	0,14
N	1,36	0,05
P	0,46	0,02
R	2,1	0,08
S	5	0,19
T	2,51	0,098
U	0,79	0,03



Pin 1 :	Anode 1
Pin 2 :	Anode 2
Pin 3 :	Gate